Satoshi Shigematsu

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/518248/publications.pdf

Version: 2024-02-01

16 papers	114 citations	6 h-index (1478505)	10 g-index (1372567)
17 all docs	17 docs citations	17 times ranked	22 citing authors

#	Article	IF	Citations
1	Hydrogen diffusion behavior in CH2P-molecular-ion-implanted silicon wafers for CMOS image sensors. Materials Science in Semiconductor Processing, 2022, 137, 106211.	4.0	1
2	Dissociation Kinetics of Trapped Hydrogen in High-dose Hydrocarbon-Molecular-Ion-Implanted Silicon during Rapid Thermal Annealing. E-Journal of Surface Science and Nanotechnology, 2022, , .	0.4	0
3	Influence of oxygen on copper gettering in hydrocarbon molecular ion implanted region using atom probe tomography. Nuclear Instruments & Methods in Physics Research B, 2020, 478, 99-103.	1.4	4
4	Hydrogen passivation for reduction of SiO₂/Si interface state density using hydrocarbon-molecular-ion-implanted silicon wafers. Japanese Journal of Applied Physics, 2020, 59, 125502.	1.5	13
5	Effect of hydrocarbon molecular ion size for amorphous region formation analyzed by X-ray photoelectron spectroscopy. Japanese Journal of Applied Physics, 2020, 59, 025510.	1.5	3
6	Molecular and Atomic Hydrogen Diffusion Behavior by Reaction Kinetic Analysis in Projection Range of Hydrocarbon Molecular Ion for CMOS Image Sensors. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1900175.	1.8	5
7	Proximity gettering technique using CH₃O multielement molecular ion implantation for the reduction of the white spot defect density in CMOS image sensor. Japanese Journal of Applied Physics, 2019, 58, 091002.	1.5	5
8	Proximity Gettering Design of Hydrocarbonâ€"Molecularâ€"Ionâ€"Implanted Silicon Wafers Using Dark Current Spectroscopy for CMOS Image Sensors. Sensors, 2019, 19, 2073.	3.8	20
9	Effect of ramping up rate on end of range defect in multielement molecular-ion (CH₃O)-implanted silicon wafers. Japanese Journal of Applied Physics, 2019, 58, 121002.	1.5	1
10	A Review of Proximity Gettering Technology for CMOS Image Sensors Using Hydrocarbon Molecular Ion Implantation. Sensors and Materials, 2019, 31, 1939.	0.5	7
11	Gettering mechanism in hydrocarbon-molecular-ion-implanted epitaxial silicon wafers revealed by three-dimensional atom imaging. Japanese Journal of Applied Physics, 2018, 57, 091302.	1.5	7
12	Room-temperature bonding of epitaxial layer to carbon-cluster ion-implanted silicon wafers for CMOS image sensors. Japanese Journal of Applied Physics, 2018, 57, 061302.	1.5	8
13	Gettering Sinks for Metallic Impurities Formed by Carbon-Cluster Ion Implantation in Epitaxial Silicon Wafers for CMOS Image Sensor. IEEE Journal of the Electron Devices Society, 2018, 6, 1200-1206.	2.1	6
14	Proximity gettering of silicon wafers using CH₃O multielement molecular ion implantation technique. Japanese Journal of Applied Physics, 2018, 57, 096503.	1.5	12
15	(Invited) Proximity Gettering Design of Hydrocarbon Molecular Ion Implanted Silicon Wafers Using Direct Bonding Technique for Advanced CMOS Image Sensors: A Review. ECS Transactions, 2018, 86, 77-93.	0.5	2
16	Trapping and diffusion behaviour of hydrogen simulated with TCAD in projection range of carbonâ€cluster implanted silicon epitaxial wafers for CMOS image sensors. Physica Status Solidi C: Current Topics in Solid State Physics, 2017, 14, .	0.8	19